

# PMDPB55XP

# 20 V, dual P-channel Trench MOSFET Rev. 3 — 4 June 2012

Product data sheet

#### 1. **Product profile**

## 1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless ultra thin DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction

## 1.3 Applications

- Charging switch for portable devices
- DC/DC converters
- Small brushless DC motor drive
- Power management in battery-driven portables
- Hard disc and computing power management

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	•						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-4.5	Α
Static charact	eristics (per transistor)						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3.4 \text{ A}; T_j = 25 \text{ °C}$		-	55	70	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	6 5 4	D1 D2 _   _
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	G1 S1 S2 G2
7	D1	drain TR1	Transparent top view	017aaa258
8	D2	drain TR2	SOT1118 (DFN2020-6)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMDPB55XP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PMDPB55XP	1Z

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-4.5	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-3.4	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C}$	<u>[1]</u>	-	-2.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb} = 25  ^{\circ}C$ ; single pulse; $t_p \le 10  \mu s$		-	-14	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	490	mW
			[1]	-	1170	mW
		T <sub>sp</sub> = 25 °C		-	8300	mW
Source-dra	in diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-1.2	Α
Per device						
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

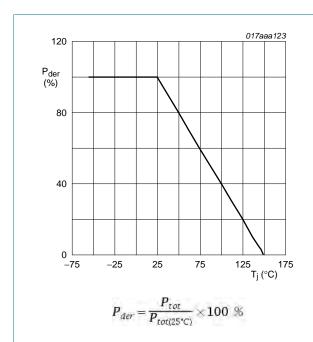


Fig 1. Normalized total power dissipation as a function of junction temperature

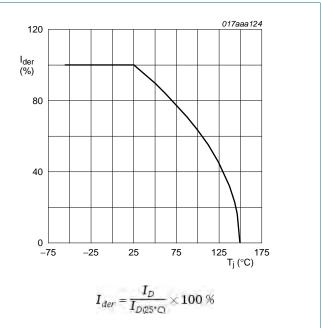
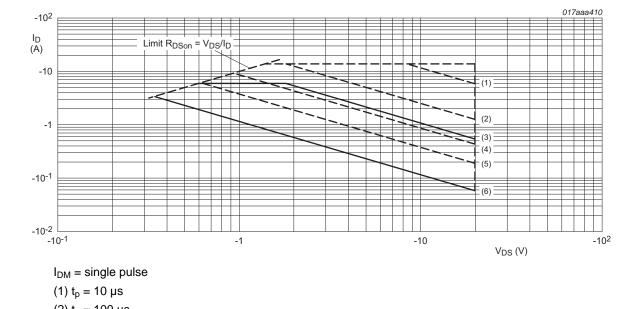


Fig 2. Normalized continuous drain current as a function of junction temperature



- (2)  $t_p = 100 \mu s$
- (3) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$
- (4)  $t_p = 10 \text{ ms}$
- $(5) t_p = 100 ms$
- (6) DC; T<sub>amb</sub> = 25 °C; drain mounting pad 6 cm<sup>2</sup>

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source Fig 3.

#### Thermal characteristics 6.

Table 6. **Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	223	256	K/W
			[2]	-	93	107	K/W
		in free air; t ≤ 5 s	[2]	-	55	63	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point	in free air		-	10	15	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

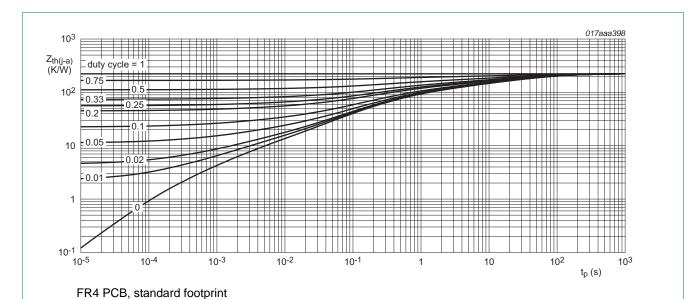
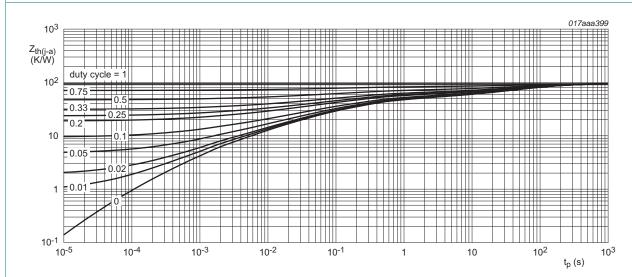


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.47	-0.65	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -3.4 \text{ A}; T_j = 25 \text{ °C}$	-	55	70	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -3.4 \text{ A}; T_j = 150 \text{ °C}$	-	78	99	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -1.6 \text{ A}; T_j = 25 \text{ °C}$	-	75	90	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.5 \text{ A}; T_j = 25 \text{ °C}$	-	110	135	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -3.4 \text{ A}; T_j = 25 \text{ °C}$	-	15	-	S
Dynamic	characteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -3.4 \text{ A}; V_{GS} = -5 \text{ V};$	-	16.5	25	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
$Q_{GD}$	gate-drain charge		-	1.65	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}$ ; f = 1 MHz; $V_{GS} = 0 \text{ V}$ ;	-	785	-	рF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	80	-	рF
C <sub>rss</sub>	reverse transfer capacitance		-	64	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = -10 \text{ V}; I_D = -3.4 \text{ A}; V_{GS} = -5 \text{ V};$	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	14	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	135	-	ns
t <sub>f</sub>	fall time		-	68	-	ns
Source-d	rain diode (per transistor)					
$V_{SD}$	source-drain voltage	$I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	-	-0.8	-1.2	V

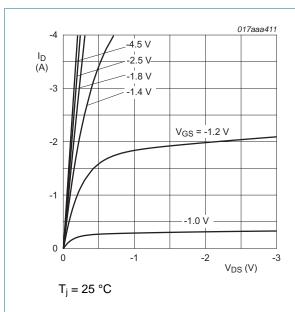


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

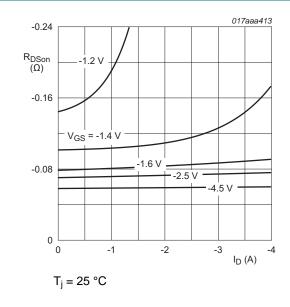
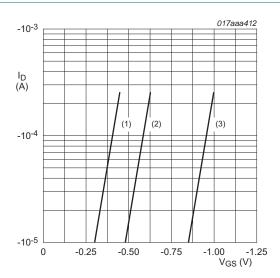


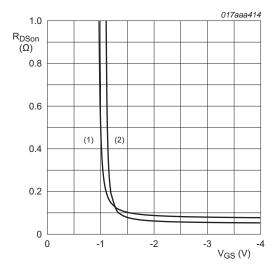
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

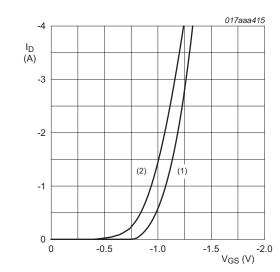


 $I_{D} = -1 A$ 

(1) 
$$T_i = 150 \, ^{\circ}C$$

(2) 
$$T_j = 25 \, {}^{\circ}\text{C}$$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

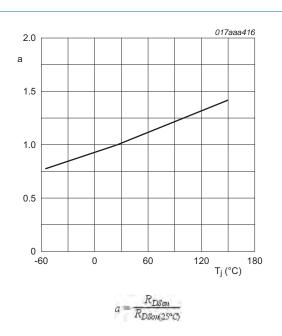
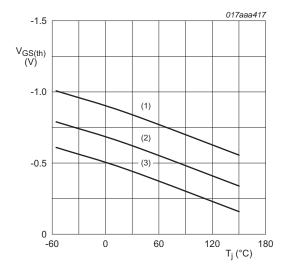


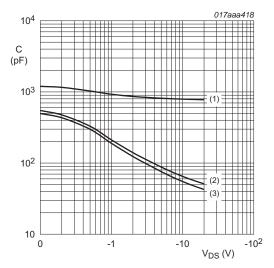
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

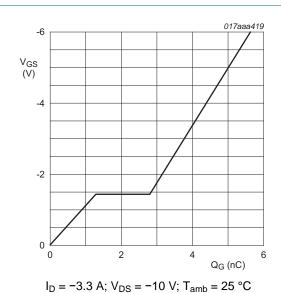
Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

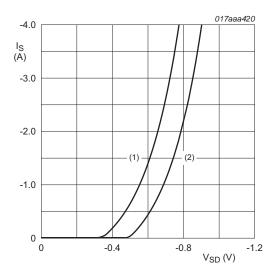
Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V<sub>GS</sub>(pl)
V<sub>GS</sub>(th)
V<sub>GS</sub>
Q<sub>GS1</sub> Q<sub>GS2</sub>
Q<sub>GS</sub> Q<sub>G</sub>(tot)
017aaa137

Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



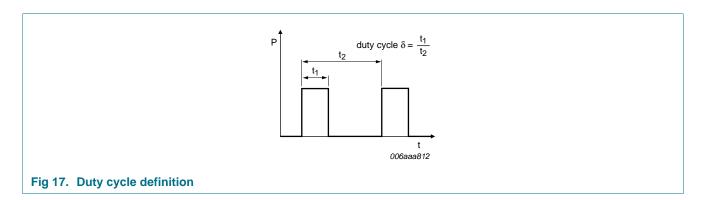
 $V_{GS} = 0 V$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ 

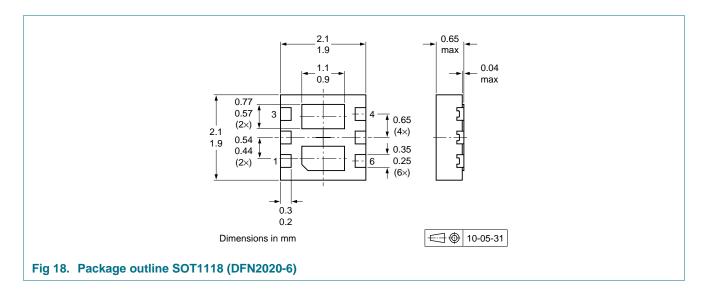
(2)  $T_{amb} = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

# 8. Test information



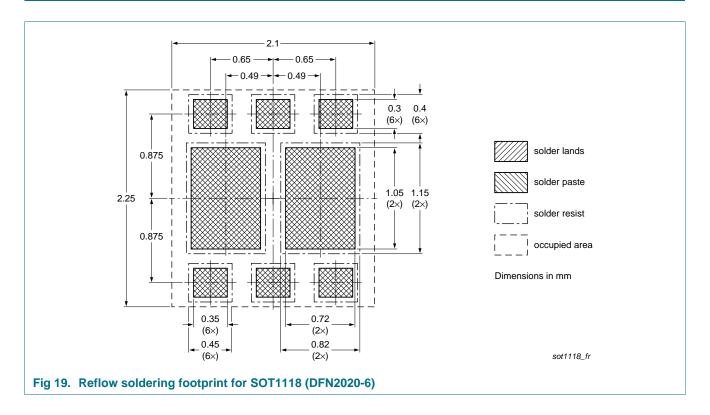
# 9. Package outline



PMDPB55XP

20 V, dual P-channel Trench MOSFET

# 10. Soldering



# 11. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB55XP v.3	20120604	Product data sheet	-	PMDPB55XP v.2
Modifications:	• <u>Table 7.</u> : V <sub>GSth</sub>	values updated		
PMDPB55XP v.2	20120502	Product data sheet	-	PMDPB55XP v.1
PMDPB55XP v.1	20120309	Product data sheet	-	-

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#### 12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **Nexperia**

# PMDPB55XP

20 V, dual P-channel Trench MOSFET

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